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				Application Number	09/759,312
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				First Named Inventor	Yoshihiro UETA
				Art Unit	2812
				Examiner Name	S. Mulpuri
Sheet	1	of	1	Attorney Docket Number	299002051800

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ³ (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear

FOREIGN PATENT DOCUMENTS					
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NON PATENT LITERATURE DOCUMENTS					
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.			²
<i>Gul</i>	1.	Zauner, A.R.A. et al. (1999). "Homoepitaxial Growth on Misoriented GaN Substrates By MOCVD," <i>Proceedings of the Material Research Society Symposium W (GaN and Related Alloys) November 28-December 3, 1999</i> , 595:407 (Abstract W6.3).			

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Examiner Signature pa-996555	<i>S. Mulpuri</i>	Date Considered <i>2/20/03</i>
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